







TLV841 JAJSKU3D - APRIL 2020 - REVISED JANUARY 2023

TLV841 小型 nanoPower 電圧監視 IC、WCSP パッケージ

1 特長

高性能設計:

- わずかな静止電流:125nA (標準値)
- 高いスレッショルド精度:±0.5% (標準値)
- 高精度ヒステリシス (V_{HYS}) を内蔵:5% (標準値)

多様なアプリケーションに対応する設計:

- 動作電圧範囲:0.7V~5.5V
- 調整可能なスレッショルド電圧:0.505V (標準値)
- 固定 (V_{IT-}) 電圧:0.8V~4.9V (0.1V 刻み)
- 独立した SENSE ピン (TLV841S)
- アクティブ LOW のマニュアル・リセット (MR) (TLV841M)
- TLV841 のプッシュ・ボタン監視 (S/M バリアント)
- リセット遅延時間をプログラム可能 (t_D):コンデンサ・ベ ースのプログラマブル (TLV841C)
 - 最小遅延時間:40µs (標準値)、コンデンサなしの 場合
- リセット遅延時間をプログラム可能 (t_D):固定時間遅延 オプション (TLV841M および TLV841S)
 - 40µs, 2ms, 10ms, 30ms, 50ms, 80ms, 100ms, 150ms, 200ms
- 温度範囲:-40℃~+125℃

複数の出力トポロジ、パッケージ・タイプ:

- TLV841xxDL:オープン・ドレイン、アクティブ LOW (RESET)
- TLV841xxPL:プッシュプル、アクティブ LOW (RESET)
- TLV841xxDH:オープン・ドレイン、アクティブ HIGH (RESET)
- TLV841xxPH:プッシュプル、アクティブ HIGH (RESET)
- パッケージ: 0.73mm x 0.73mm DSBGA

2 アプリケーション

- ウェアラブルや補聴器などのパーソナル・エレクトロニ クス
- ホーム・シアターおよびエンターテインメント
- **POS** システム
- グリッド・インフラストラクチャ
- データ・センターおよびエンタープライズ・コンピューテ イング

3 概要

TLV841 は、超小型の DSBGA パッケージに ±0.5% のス レッショルド精度を備えたナノパワー高精度電圧監視 IC です。TLV841 には 3 つのピン配置バリエーション (S、 M、C) があり、クラス最小のソリューション・サイズで多くの 独自オプションを提供します。ヒステリシスに加えてプログ ラム可能な遅延が内蔵されているので、電圧レールやプッ シュ・ボタン信号を監視するときに誤リセット信号が発生す ることを防止できます。 TLV841S のアクティブ LOW 出力 では、SENSE ピンと RESET ピンの間に外付け抵抗を追 加することで、電圧スレッショルドのヒステリシスを増やすこ とができます。 TLV841 は、高精度、低消費電力、クラス最 高の機能を最小のコンパクトなフォーム・ファクタで実現し ており、パーソナル製品やコンシューマ製品など、幅広い バッテリ駆動アプリケーションに最適なソリューションを提 供します。

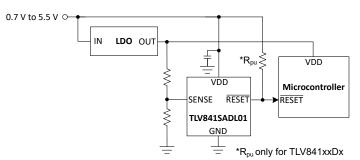
VDD ピンと SENSE ピンが別になっているので (TLV841S)、高信頼性システムで求められる冗長性を実 現できます。SENSE が VDD から分離されており、VDD 以外のレール電圧を監視することも、プッシュボタン入力と して使用することもできます。 SENSE ピンは高インピーダ ンス入力なので外付け抵抗を使うこともできます。 TLV841S は、外付けコンデンサなしで固定リセット遅延タ イミング・オプションを提供します。TLV841C を使用する と、CT ピンがフローティングのままになっているときの最小 遅延を含め、リセット時間遅延をプログラム可能です。 TLV841M には独立したマニュアル・リセット (MR) ピンが あり、外部信号で強制的にリセット状態にすることも、プッ シュ・ボタン入力として使用することも可能です。 TLV841M は、VDD および MR ピン監視用に設定できるので、シン プルな 2 チャネル監視回路ソリューションを作成できま す。TLV841 は、-40℃~+125℃ (T_A) の温度範囲で動作 します。

製品情報

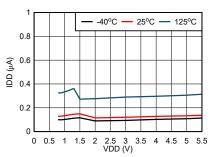
部品番号	パッケージ ⁽¹⁾	本体サイズ (公称)
TLV841	DSBGA (4)	0.73mm×0.73mm

パッケージの詳細については、このデータシートの末尾の外形図 を参照してください。





代表的なアプリケーション回路



標準消費電流



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5 Device Comparison

図 5-1 shows the device naming nomenclature to compare the different device variants. See 表 12-1 for a more detailed explanation. Please contact Texas Instruments for availability of variant options.

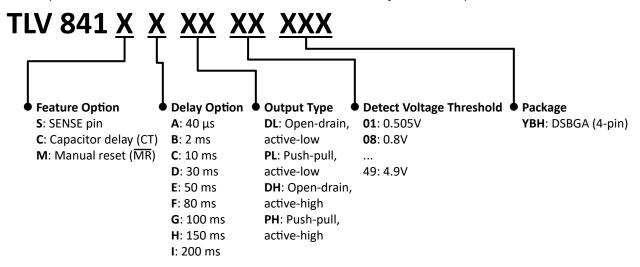


図 5-1. Device Naming Nomenclature



6 Pin Configuration and Functions

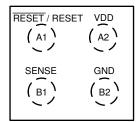


図 6-1. YBH 4-Pin DSBGA Package (TLV841S) Top View

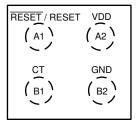


図 6-2. YBH 4-Pin DSBGA Package (TLV841C) Top View

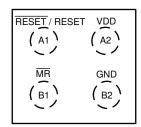


図 6-3. YBH 4-Pin DSBGA Package (TLV841M) Top View

表 6-1. Pin Functions

PIN		I/O	DESCRIPTION		
PIN NO.	TLV841S	TLV841C	TLV841M	1/0	DESCRIPTION
A1	RESET	RESET	RESET	0	Active-Low Output Reset Signal for TLV841xxxL: This pin is driven logic low when VDD and SENSE voltage falls below the negative voltage threshold (V_{IT} .) or when the \overline{MR} voltage falls below the logic low threshold. \overline{RESET} remains logic low (asserted) until \overline{MR} is above the logic high threshold or for the duration of the delay time period (t_D) after VDD or SENSE voltage rises above V_{IT} + V_{HYS}
A1	RESET	RESET	RESET	0	Active-High Output Reset Signal for TLV841xxxH: This pin is driven logic high when VDD or SENSE voltage falls below the negative voltage threshold (V_{IT}) or when the \overline{MR} voltage falls below the logic low threshold. RESET remains logic high (asserted) until \overline{MR} is above the logic high threshold or for the duration of the delay time period (t_D) after VDD or SENSE voltage rises above V_{IT} + V_{HYS}
A2	VDD	VDD	VDD	I	Input Supply Voltage: The VDD pin connects to the power supply to power the device. TLV841C and TLV841M monitor VDD voltage. TLV841S monitors SENSE only. Good analog design practice recommends placing a minimum 0.1 μF ceramic capacitor as near as possible to the VDD pin.
B1	SENSE	-	-	ı	SENSE pin : This pin is connected to the voltage to be monitored. When the voltage on SENSE falls below the negative threshold voltage $V_{\text{IT-}}$, reset asserts. When the voltage on SENSE rises above the positive threshold voltage ($V_{\text{IT-}} + V_{\text{HYS}}$), reset deasserts. For noisy applications, placing a 10 nF to 100 nF ceramic capacitor close to this pin may be needed for optimum performance.
B1	-	СТ	_ I delay time. Connect		Capacitor Time Delay Pin: The CT pin offers a user-programmable reset deassert delay time. Connect an external capacitor on this pin to adjust time delay. When not in use leave pin floating for the smallest fixed time delay.
B1	-	-	MR	ı	Manual Reset : Pull this pin to a logic low to assert a reset signal in the RESET output pin (RESET signal for DL and PL option). After MR pin is left floating or pulls to logic high, the RESET output deasserts to the nominal state after the reset delay time (t _D)expires. If unused, the pin can be left floating or connected to VDD.
B2	GND	GND	GND	_	Ground

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7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range, unless otherwise noted(1)

		MIN	MAX	UNIT
Voltage	VDD, SENSE (TLV841S)	-0.3	6	V
Voltage	CT (TLV841C), MR (TLV841M), RESET (TLV841xxPx), RESET (TLV841xxPx)	-0.3	V _{DD} +0.3 ⁽³⁾	V
	RESET (TLV841xxDx), RESET (TLV841xxDx)	-0.3	6	
Current	RESET, RESET		±20	mA
Temperature ⁽²⁾	Operating ambient temperature, T _A	-40	125	°C
Temperature	Storage, T _{stg}	-65	150	C

- (1) Stresses beyond those listed under Absolute Maximum Rating may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Condition. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) As a result of the low dissipated power in this device, it is assumed that $T_J = T_A$.
- (3) The absolute maximum rating is (VDD + 0.3) V or 6 V, whichever is smaller

7.2 ESD Ratings

			VALUE	UNIT	
V _(ESD)	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾		± 2000	V	
	Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	± 750	V	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	,	MIN	NOM MAX	UNIT
	VDD (TLV841C, TLV841M)	0.7	5.5	
	VDD (TLV841S)	0.85	5.5	
	VDD (TLV841xxPH)	1	5.5	
Voltage	SENSE	0	5.5	V
	MR (1), CT	0	V_{DD}	
	RESET(TLV841xxPL), RESET (TLV841xxPH)	0	V_{DD}	
	RESET(TLV841xxDL), RESET (TLV841xxDH)	0	5.5	
Current	RESET, RESET	-5	5	mA
T _A	Operating free air temperature	-40	125	°C
C _{CT}	CT pin capacitor range	0	10	μF

(1) If the logic signal driving MR is less than V_{DD}, then additional current flows into VDD and out of MR. MR pin voltage should not be higher than V_{DD}.



7.4 Thermal Information

		TLV841	
	THERMAL METRIC ⁽¹⁾	YBH (WCSP)	UNIT
		4 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	180.8	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	1.8	°C/W
R _{0JB}	Junction-to-board thermal resistance	58.0	°C/W
ΨЈТ	Junction-to-top characterization parameter	0.9	°C/W
ΨЈВ	Junction-to-board characterization parameter	58.0	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



7.5 Electrical Characteristics

At $V_{DDMIN} \le V_{DD} \le 5.5$ V, CT = \overline{MR} = Open, $\overline{RESET}/RESET$ pull-up resistor $R_{pull-up}$ (3) = 100 k Ω to VDD, output reset load C_{LOAD} = 10 pF and over the operating free-air temperature range –40°C to 125°C, unless otherwise noted. Typical values are at T_A = 25°C

	PARAMETER	TES	T CONDITIONS	MIN	TYP	MAX	UNIT
соммо	N PARAMETERS						
V _{ADJ-VIT-}	Negative-going input threshold for TLV841Sxxx01 ADJ version				0.505		V
V _{IT}	Negative-going input threshold range Fixed threshold version (1)	ge		0.8		4.9	V
V _{IT- ACC}	Negative-going input threshold according	/=	841Sxx01) or 0.8 V to 1.7 V	-2.5	±0.5	2.5	%
_		V _{IT} = 1.8 V to 4.9 V	(Fixed threshold)	-2	±0.5	2	
V _{HYS}	Hysteresis on V _{IT} pin	V _{IT} = 0.505 V and 0).8 V	3	5	8	%
VHYS		$V_{IT-} = 0.9 \text{ V to } 4.9 \text{ V}$	1	3	5	7	/0
V_{POR}	Power on reset voltage ⁽²⁾	TLV841xxxLxx	$V_{OL(MAX)} = 300 \text{ mV}$ $I_{RESET(Sink)} = 15 \mu\text{A}$			700	mV
V POR	Power officeset voltage (-)	TLV841xxxHxx	$V_{OH(MIN)} = 0.8VDD$ $I_{RESET(Source)} = 15 \mu A$			900	
			$V_{DD} = 0.85 \text{ V}$ $I_{RESET(Sink)} = 15 \mu\text{A}$ $I_{RESET(Sink)} = 15 \mu\text{A}$			300	mV
V_{OL}	Low level output voltage		$V_{DD} = 3.3 \text{ V}$ $I_{RESET(Sink)} = 2 \text{ mA}$ $I_{RESET(Sink)} = 2 \text{ mA}$			300	mV
			$V_{DD} = 5.5 \text{ V}$ $I_{RESET(Sink)} = 2 \text{ mA}$ $I_{RESET(Sink)} = 2 \text{ mA}$			300	mV
			$V_{DD} = 1 V$ $I_{RESET(Source)} = 15 \mu A$ $I_{RESET(Source)} = 15 \mu A$	0.8V _{DD}			V
V_{OH}	High level output voltage		V_{DD} = 1.8 V $I_{RESET(Source)}$ = 500 μ A $I_{RESET(Source)}$ = 500 μ A	0.8V _{DD}			V
			$V_{DD} \ge 3.3 \text{ V}$ $I_{RESET(Source)} = 2 \text{ mA}$ $I_{RESET(Source)} = 2 \text{ mA}$	0.8V _{DD}			V
lu(OD)	Open-Drain output leakage current	V _{DD} = V _{PULLUP} = 5.5	$T_A = -40^{\circ}\text{C to } 85^{\circ}\text{C}$		10	100	nA
I _{lkg(OD)}	Open-Diam output leakage cullent	V DD - V PULLUP - 3.3			10	350	11/
I _{DD}	Supply current into VDD pin Supply current into VDD pin	nt $V_{DD} = 5.5 \text{ V}$ $V_{IT-} = 1.9 \text{ V to } 4.9 \text{ V}$,		0.125	1	μA

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7.5 Electrical Characteristics (continued)

At $V_{DDMIN} \le V_{DD} \le 5.5$ V, CT = \overline{MR} = Open, $\overline{RESET}/RESET$ pull-up resistor $R_{pull-up}$ (3) = 100 k Ω to VDD, output reset load C_{LOAD} = 10 pF and over the operating free-air temperature range $-40^{\circ}C$ to 125°C, unless otherwise noted. Typical values are at T_A = 25°C

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
TLV841S	LV841S								
	Current into SENSE pin, fixed threshold variant	V _{DD} = V _{SENSE} = 5.5 V V _{IT} = 0.8 V to 4.9 V	0.025		0.1				
ISENSE	Current into SENSE pin, ADJ variant	$V_{DD} = V_{SENSE} = 5.5 \text{ V}$ $V_{IT-} = 0.505 \text{ V}$		0.025	0.05	μA			
TLV841N	ĺ				•				
V _{MR_L}	Manual reset logic low input				$0.3V_{DD}$	V			
$V_{\overline{MR}_H}$	Manual reset logic high input		0.7V _{DD}			V			
$R_{\overline{MR}}$	Manual reset internal pull-up resistance			100		kΩ			
TLV841C	FLV841C								
R _{CT}	CT pin internal resistance		410	500	590	kΩ			

⁽¹⁾ V_{IT} threshold voltage range from 0.8 V to 4.9 V (for DL, PL, DH) and 1 V to 4.9 V (for PH) in 100 mV steps, for released versions see Device Voltage Thresholds table.

⁽²⁾ V_{POR} is the minimum V_{DD} voltage level for a controlled output state.

⁽³⁾ Pull up resistance applicable for open drain variants



7.6 Timing Requirements

At $V_{DDMIN} \le V_{DD} \le 5.5$ V, CT = \overline{MR} = Open, \overline{RESET} pull-up resistor $R_{pull-up}$ = 100 k Ω to VDD, output load is C_{LOAD} = 10 pF and over the operating free-air temperature range –40°C to 125°C, unless otherwise noted. Typical values are at T_A = 25°C

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{P_HL}	Propagation detect delay for V _{DD} falling below V _{IT}	$V_{DD} = (V_{IT+} + 10\%)$ to $(V_{IT-} - 10\%)^{(2)}$		30	50	μs
		CT pin = Open or NC		40	80	μs
t _D	Reset time delay (TLV841C variant)	CT pin = 10 nF		6.2		ms
		CT pin = 1 µF		619		ms
		Variant A (3)		40	80	μs
		Variant B (3)		2		ms
		Variant C (3)		10		ms
	Reset time delay (TLV841S and TLV841M variant) ⁽⁵⁾	Variant D (3)		30		ms
t _D		Variant E (3)		50		ms
		Variant F (3)		80		ms
		Variant G ⁽³⁾		100		ms
		Variant H (3)		150		ms
		Variant I (3)		200		ms
t _{GI_VIT}	Glitch immunity V _{IT}	5% V _{IT} overdrive ⁽⁴⁾		10		μs
t _{STRT}	Startup Delay ⁽¹⁾				300	μs
t _{MR_RES}	Propagation delay from MR low to reset	V _{DD} = 3.3 V, MR < V _{MR_L}		t _{P_HL}		μs
t _{MR_tD}	Delay from release MR to deassert reset	$V_{DD} = 3.3 \text{ V},$ $\overline{\text{MR}} = V_{\overline{\text{MR}}_{-}\text{L}} \text{ to } V_{\overline{\text{MR}}_{-}\text{H}}$		t _D		ms
t _{MR_PW}	Glitch immunity MR pin			10		μs

⁽¹⁾ When VDD starts from less than the specified minimum V_{DD} and then exceeds V_{POR} , reset is release after the startup delay (t_{STRT}). For TLV841C variants a capacitor at CT pin will add t_D delay to t_{STRT} time

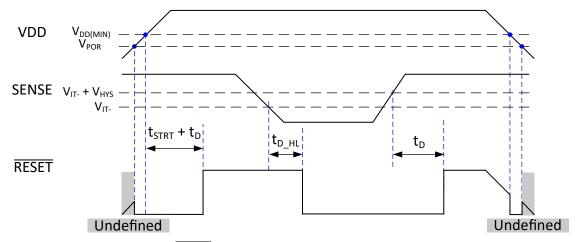
⁽²⁾ t_{P HL} measured from threhold trip point (V_{IT}) to V_{OL} for active low variants and V_{OH} for active high variants.

⁽³⁾ Refer device nomenclature table for variant description. V_{DD} transition from V_{IT} – 10% to V_{IT+} + 10% for TLV841M and TLV841C; V_{SENSE} transition from V_{IT} – 10% to V_{IT+} + 10% for TLV841S

⁴⁾ Overdrive % = $[(V_{DD}/V_{IT-}) - 1] \times 100\%$ for TLV841M and TLV841C; Overdrive % = $[(V_{SENSE}/V_{IT-}) - 1] \times 100\%$ for TLV841S

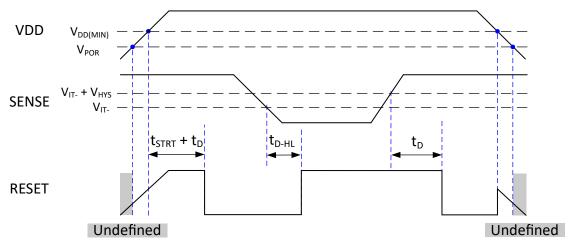
⁽⁵⁾ Specified by design and characterization

7.7 Timing Diagrams



A. Open-Drain timing diagram assumes the RESET pin is connected via an external pull-up resistor to VDD.

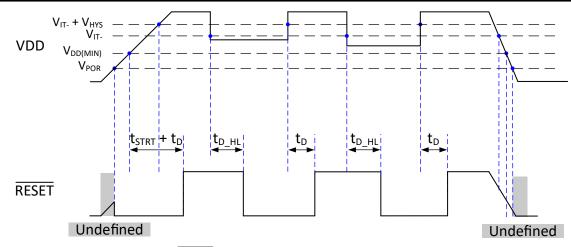
図 7-1. Timing Diagram for TLV841SxxL (SENSE) Active Low Output [Open-Drain and Push-Pull Output Topology]



A. Open-Drain timing diagram assumes the RESET pin is connected via an external pull-up resistor to VDD.

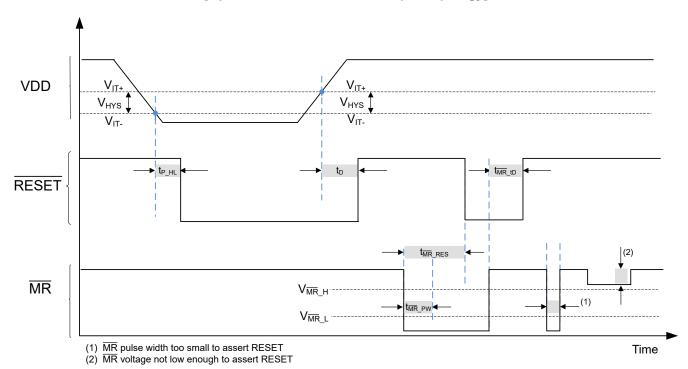
図 7-2. Timing Diagram for TLV841SxxH (SENSE) Active High Output [Open-Drain and Push-Pull Output Topology]





- A. Open-Drain timing diagram assumes the RESET / RESET pin is connected via an external pull-up resistor to VDD.
- B. $t_{D \text{ (no cap)}}$ is included in t_{STRT} time delay. If t_D delay is programmed by an external capacitor connected to CT pin then t_D programmed time will be added to the startup time, VDD slew rate = 1 V / μ s.
- C. Be advised that the VDD falling slew rate is (slew rate > 1 V / μ s) and resulting RESETin what is shown above figure. The RESET behavior would be similar to $\boxed{2}$ 7-1 if the slew rate was much slower or if VDD decay time is larger than the prop delay (t_D HL).

図 7-3. Timing Diagram for TLV841CxxL (CT) Active Low Output [Open-Drain and Push-Pull Output Topology]

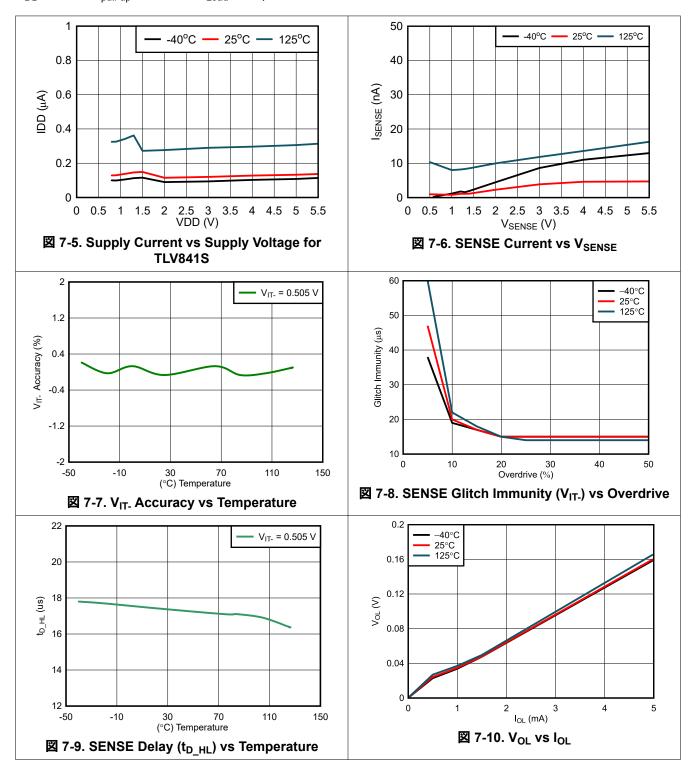


 $A. \quad \text{Open-Drain timing diagram assumes the } \overline{\text{RESET}} \, / \, \text{RESET pin is connected via an external pull-up resistor to VDD}.$

図 7-4. Timing Diagram for TLV841MxxL Active Low Output (MR)
[Open-Drain and Push-Pull Output Topology]

7.8 Typical Characteristics

Typical characteristics show the typical performance of the TLV841 device. Test conditions are T_A = 25°C, V_{DD} = 3.3 V, $R_{pull-up}$ = 100 k Ω , C_{Load} = 50 pF, unless otherwise noted.



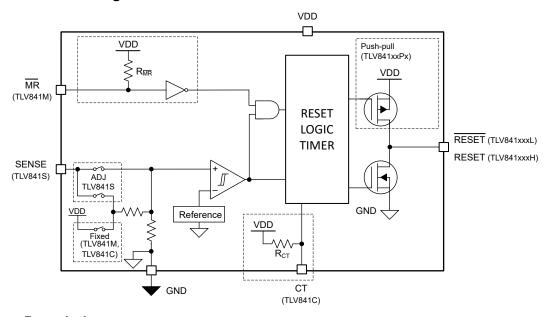
8 Detailed Description

8.1 Overview

The TLV841 is a family of very small, accurate, nano-quiescent current voltage supervisors with fixed threshold voltages. TLV841S features a separate SENSE pin for adjustable voltage threshold without losing accuracy, TLV841C features a programable reset time delay using external capacitor, and TLV841M features an active-low manual reset ($\overline{\text{MR}}$). The TLV841 family provide $\pm 0.5\%$ typical monitor threshold accuracy with hysteresis and glitch immunity.

The adjustable variant of TLV841S has an internal reference voltage of 0.505 V and can be used to accurately monitor any voltage above 0.505 V within the recommended operating conditions. In addition to the adjustable threshold variant, fixed negative threshold voltages (V_{IT-}) can be factory set from 0.8 V to 4.9 V in 100 mV steps. TLV841 is available in a very small (0.73 mm x 0.73 mm) 4-pin BGA package.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Input Voltage (VDD)

For TLV841C and TLV841M, the VDD pin is monitored by the internal comparator to indicate when VDD falls below the fixed threshold voltage. For TLV841S, the SENSE pin is monitored by the internal comparator. VDD also functions as the supply for the internal bandgap, internal regulator, state machine, buffers and other control logic blocks. Good design practice involve placing a 0.1 μ F to 1 μ F bypass capacitor at VDD input for noisy applications to ensure enough charge is available for the device to power up correctly.

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8.3.1.1 VDD Hysteresis

The internal comparator has built-in hysteresis to avoid erroneous output reset release. If the voltage at the VDD (TLV841C, TLV841M) pin falls below $V_{\text{IT-}}$ the output reset is asserted. When the monitored voltage goes above $V_{\text{IT-}}$ plus hysteresis (V_{HYS}) the output reset is deasserted after t_D delay.

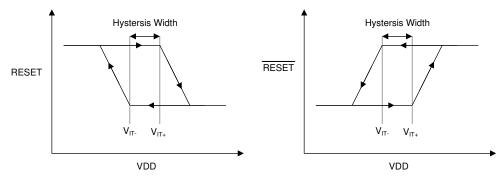


図 8-1. Hysteresis Diagram

8.3.1.2 VDD Transient Immunity

The TLV841 is immune to quick voltage transients or excursion on VDD. Sensitivity to transients depends on both pulse duration (t_{Gl_VIT}), specified in to posterior 7.6, and overdrive. Overdrive is defined by how much VDD deviates from the specified threshold. Threshold overdrive is calculated as a percent of the threshold in question, as shown in to posterior 7.6.

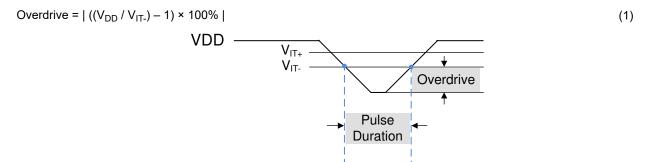


図 8-2. Overdrive vs Pulse Duration

8.3.2 SENSE Input (TLV841S)

The SENSE input can vary from 0 V to 5.5 V, regardless of the device supply voltage used. The SENSE pin is used to monitor a critical voltage rail or push-button input. If the voltage on this pin drops below V_{IT-} , then RESET/RESET is asserted. When the voltage on the SENSE pin rises above the positive threshold voltage $V_{IT-} + V_{HYS}$, RESET/RESET deasserts after the user-defined RESET/RESET delay time. The internal comparator has built-in hysteresis to ensure well-defined RESET/RESET assertions and deassertions even when there are small changes on the voltage rail being monitored.

8.3.2.1 SENSE Hysteresis

The internal comparator has built-in hysteresis to avoid erroneous output reset release. If the voltage at the SENSE (TLV841S) pin falls below V_{IT-} the output reset is asserted. When the monitored voltage goes above V_{IT-} plus hysteresis (V_{HYS}) the output reset is deasserted after t_D delay.

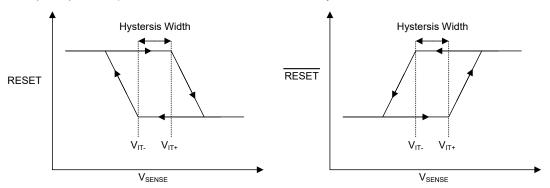


図 8-3. Hysteresis Diagram

8.3.2.2 Immunity to SENSE Pin Voltage Transients

The TLV841S is immune to short voltage transient spikes or excursion on the SENSE pin. To further improve the noise immunity on the SENSE pin, placing a 10 nF to 100 nF capacitor between the SENSE pin and GND can reduce the sensitivity to sensitivity to transient voltages on the monitored signal.

Sensitivity to transients depends on both transient duration and overdrive (amplitude) on the transient voltage. Overdrive is defined by how much V_{SENSE} exceeds the specified threshold and is important to know because the smaller the overdrive, the slower the resonse of the output. Threshold overdrive is calculated as a percent of the threshold in question, as shown in $\stackrel{\sim}{\gtrsim} 2$.

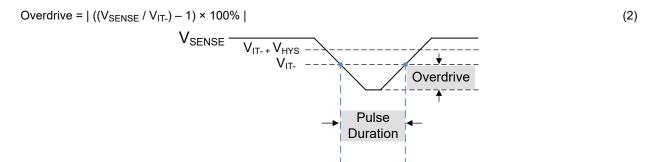


図 8-4. Overdrive vs Pulse Duration

8.3.3 User-Programmable Reset Time Delay for TLV841C only

The reset time delay can be set to a typical value of 40 μ s by leaving the CT pin floating, or a maximum value of approximately 6.2 seconds by connecting 10 μ F delay capacitor. The reset time delay (t_D) can be programmed by connecting a capacitor no larger than 10 μ F between the CT pin and GND.

The relationship between external capacitor ($C_{CT_EXT~(typ)}$) in μF at CT pin and the time delay ($t_{D~(typ)}$) in seconds is given by ± 3 .

$$t_{D (typ)} = -ln (0.29) \times R_{CT (typ)} \times C_{CT EXT (typ)} + t_{D (no cap, typ)}$$
 (3)

式 3 is simplified to 式 4 by plugging $R_{CT (typ)}$ and $t_{D (no cap, typ)}$ given in セクション 7.5 and セクション 7.6:

$$t_{D (typ)} = 618937 \times C_{CT EXT (typ)} + 40 \mu s$$
 (4)

ightharpoonup 5 solves for external capacitor value $C_{CT\ EXT}$ in units of μF where $t_{D\ (typ)}$ is in units of seconds

$$C_{CT_EXT} = (t_{D (typ)} - 40 \mu s) \div 618937$$
 (5)

The reset delay varies according to three variables: the external capacitor C_{CT_EXT} , CT pin internal resistance R_{CT} provided in $\forall 2/2 \forall 3/2 > 7.5$, and a constant. The maximum variance due to the constant is show in \vec{x} 6:

$$t_{D (max)} = -ln (0.25) x R_{CT (max)} x C_{CT (max)} + t_{D (no cap, max)}$$
 (6)

The recommended maximum delay capacitor for the TLV841C is limited to 10 μ F as this ensures enough time for the capacitor to fully discharge when a voltage fault occurs. Also, having a too large of a capacitor value can cause very slow charge up (rise times) and system noise can cause the the internal circuit to trip earlier or later near the threshold. This leads to variation in time delay where it can make the delay accuracy worse in the presence of system noise.

When a voltage fault occurs, the previously charged up capacitor discharges and if the monitored voltage returns from the fault condition before the delay capacitor discharges completely, the delay will be shorter than expected. The capacitor will begin charging from a voltage above zero and resulting in shorter than expected time delay. A larger delay capacitor can be used so long as the capacitor has enough time to fully discharge during the duration of the voltage fault. The amount of time required to discharge the delay capacitor relative to the reset delay rises as VDD fault undervoltage increases as shown in \boxtimes 8-5. From the graph below, to ensure the C_{CT_EXT} capacitor is fully discharged, the time period or duration of the voltage fault needs to be greater than 10% of the programmed reset time delay.

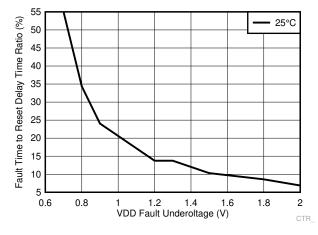


図 8-5. C_{CT_EXT} Discharge Time During Fault Condition ($C_{CT_EXT} = 1 \mu F$)

8.3.4 Manual Reset (MR) Input for TLV841M only

The manual reset ($\overline{\text{MR}}$) input allows a processor GPIO or other logic circuits to initiate a reset. A logic low on $\overline{\text{MR}}$ with pulse duration longer than $t_{\overline{\text{MR}}_{-}RES}$ will causes reset output to assert. After $\overline{\text{MR}}$ returns to a logic high ($V_{\overline{\text{MR}}}$ H) and VDD is above $V_{\overline{\text{IT}}}$, reset is deasserted after the user programmed reset time delay (t_{D}) expires.

If \overline{MR} is not controlled externally, then \overline{MR} can be left disconnected. If the logic signal controlling \overline{MR} is less than VDD, then additional current flows from VDD into \overline{MR} internally. For minimum current consumption, drive \overline{MR} to either VDD or GND. $V_{\overline{MR}}$ should not be higher than VDD voltage.

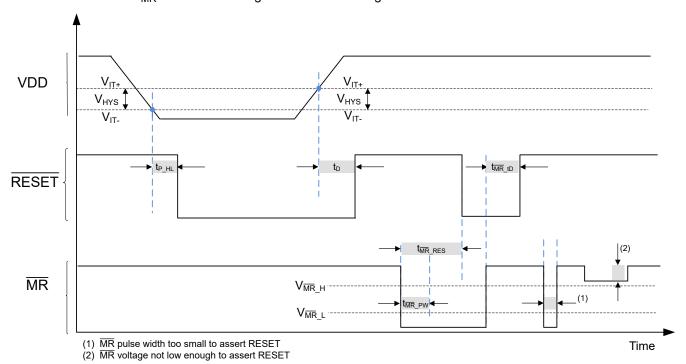


図 8-6. Timing Diagram MR and RESET (TLV841M)

8.3.5 Output Logic

8.3.5.1 RESET Output, Active-Low

RESET (Active-Low) applies to TLV841xxDL (Open-Drain) and TLV841xxPL (Push-Pull) hence the "L" in the device name. \overline{RESET} remains high (deasserted) as long as VDD/SENSE is above the negative threshold (V_{IT-}) and the \overline{MR} pin is floating or above V_{MR_H}. If VDD/SENSE falls below the negative threshold (V_{IT-}) or if \overline{MR} is driven low, then \overline{RESET} is asserted.

When \overline{MR} is again logic high or floating and VDD/SENSE rise above V_{IT+} (V_{IT-} + V_{HYS}), the delay circuit will hold \overline{RESET} low for the specified reset time delay (t_D). When the reset time delay has elapsed, the \overline{RESET} pin goes back to logic high voltage V_{OH} .

The TLV841xx**D**L (Open-Drain) version, denoted with "**D**" in the device name, requires an external pull-up resistor to hold \overline{RESET} pin high. Connect the external pull-up resistor to the desired pull-up voltage source and \overline{RESET} can be pulled up to any voltage up to 5.5 V independent of the VDD voltage. To ensure proper voltage levels, give some consideration when choosing the external pull-up resistor values. The external pull-up resistor value determines the actual V_{OL} , the output capacitive loading, and the output leakage current ($I_{Ikq(OD)}$).

The Push-Pull variant (TLV841xxPL), denoted with "P" in the device name, does not require an external pull-up resistor

8.3.5.2 RESET Output, Active-High

RESET (active-high), denoted with no bar above the pin label, applies only to TLV841xxDH (open-drain) and TLV841xxPH (push-pull) active-high version, hence the "H" in the device name. RESET remains low (deasserted) as long as VDD/SENSE is above the threshold (V_{IT-}) and the manual reset signal (\overline{MR}) is floating or above $V_{\overline{MR}_H}$. If VDD/SENSE falls below the negative threshold (V_{IT-}) or if \overline{MR} is driven low, then RESET is asserted driving the RESET pin to high voltage V_{OH} .

When \overline{MR} is again logic high or floating and VDD/SENSE is above V_{IT+} (V_{IT-} + V_{HYS}) the delay circuit will hold RESET high for the specified reset time delay (t_D). When the reset time delay has elapsed, the RESET pin goes back to low voltage V_{OL}

The TLV841xx**D**H (Open-Drain) version, denoted with "**D**" in the device name, requires an external pull-up resistor to hold \overline{RESET} pin high. Connect the external pull-up resistor to the desired pull-up voltage source and \overline{RESET} can be pulled up to any voltage up to 5.5 V independent of the VDD voltage. To ensure proper voltage levels, give some consideration when choosing the external pull-up resistor values. The external pull-up resistor value determines the actual V_{OI} , the output capacitive loading, and the output leakage current ($I_{Iko(OD)}$).

The Push-Pull variant (TLV841xxPH), denoted with "P" in the device name, does not require an external pull-up resistor



8.4 Device Functional Modes

表 8-1 and 表 8-2 summarizes the various functional modes of the device. Logic high is represented by "H" and logic low is represented by "L".

表 8-1. Truth Table for TLV841S

VDD	SENSE	RESET (ACTIVE-HIGH)	RESET (ACTIVE-LOW)
VDD < V _{POR}	_	Undefined	Undefined
$V_{POR} < V_{DD} < V_{DD(MIN)}$ (1)	_	Н	L
$VDD \ge V_{DD(MIN)}$	V _{SENSE} < V _{IT-}	Н	L
$VDD \ge V_{DD(MIN)}$	V _{SENSE} > V _{IT-} + V _{HYS}	L	Н

⁽¹⁾ When V_{DD} falls below $V_{DD(MIN)}$, undervoltage-lockout (UVLO) takes effect and RESET is held logic low (RESET is held logic high) until V_{DD} falls below V_{POR} at which the RESET/RESET output is undefined.

表 8-2. Truth Table for TLV841M

VDD	MR	RESET (ACTIVE-HIGH)	RESET (ACTIVE-LOW)
VDD < V _{POR}	_	Undefined	Undefined
V _{POR} < V _{DD} < V _{IT}	_	Н	L
VDD ≥ V _{IT-}	L	Н	L
VDD ≥ V _{IT-}	Н	L	Н
VDD ≥ V _{IT-}	Floating	L	Н

8.4.1 Normal Operation ($V_{DD} > V_{POR}$)

When VDD is greater than V_{POR} , the reset signal is determined by the voltage on the VDD pin with respect to the trip point (V_{IT-})

- MR high: The reset signal corresponds to VDD with respect to the threshold voltage.
- MR low: In this mode, the reset is asserted regardless of the threshold voltage.

8.4.2 Below Power-On-Reset (V_{DD} < V_{POR})

When the voltage on VDD is lower than V_{POR} , the device does not have enough bias voltage to internally pull the asserted output low or high and reset voltage level is undefined.

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9 Application and Implementation

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9.1 Application Information

The following sections describe in detail how to properly use this device, depending on the requirements of the final application.

9.2 Typical Application

Design 1: Adjustable Voltage Supervisor with Push-Button Functionality

A typical application for the TLV841S is voltage rail monitoring with push-button functionality. In this design application, the TLV841SADL01 is being used to monitor a 3.3 V power rail and will trigger a reset when the voltage drops below 2.90 V or when the push-button is pressed. The reset output connects to an MCU for system resetting or servicing the push-button.

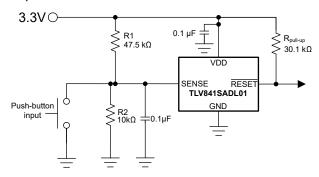


図 9-1. Design 1 - Adjustable Voltage Supervisor with Push-Button Functionality Circuit

9.2.1 Design Requirements

The design requirements, described in 表 9-1, for this design has a defined reset threshold voltage of 2.90 V, a reset delay of 40 µs and an output current no larger than 150 µA.

表 9-1. Design Requirements

PARAMETER	DESIGN REQUIREMENTS	DESIGN RESULTS
Reset Asserting	Reset needs to assert when under the reset condition of a button press or VDD ≤ 2.90 V.	Reset asserted when under the reset condition of a button pressed or VDD ≤ 2.90 V.
Reset Asserting Timing	Reset output needs to assert when the reset conditions are met for 20 μ s, and needs to de-assert after 40 μ s of no reset conditions.	Reset output asserted when the reset conditions were met for 26.4 μs and deasserted after 46.8 μs of no reset conditions.
Output Current	The output current must not exceed 150 μA.	The output current was 110 μA under the reset condition.

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9.2.2 Detailed Design Procedure

The TLV841SADL01 can monitor any voltage above 0.505 V using an external voltage divider. This device has a negative going input threshold voltage of 0.505 V; however, the design needs to assert a reset when VDD drops below 2.90 V. By using a resistor divider (R1 = 47.5 k Ω , R2 = 10 k Ω) the negative going threshold voltage becomes 2.90 V. The device's positive going voltage threshold is V_{IT}. + V_{HYS}. The typical V_{HYS} is 25 mV. This in combination with the resistor divider makes the design's positive going threshold voltage equal to 3.05 V. If VDD falls below 2.90 V, RESET will assert. If VDD rises above 3.05 V, RESET will deassert. See \boxtimes 9-2 for a timing diagram detailing the voltage levels and reset assertion/deassertion conditions.

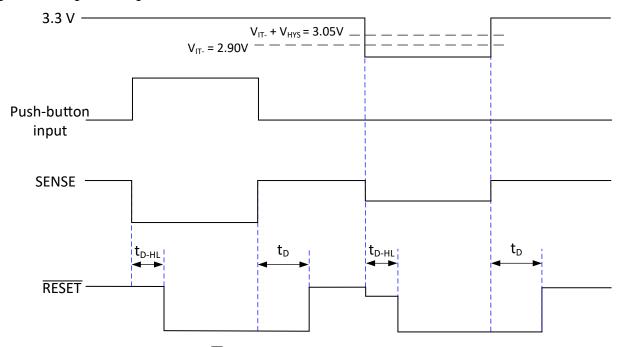


図 9-2. Design 1 Timing Diagram

This design will also enter a reset condition when the "push-button input" is asserted. The push-button is tied to ground and when pressed will drop the SENSE voltage to 0 V, making the device assert a reset. As a good analog practice, a $0.1~\mu F$ capacitor was also placed on VDD.

The desired reset timing conditions are sense propagation delay time (t_{P_HL} of 25 µs (how long it takes to assert $\overline{\text{RESET}}$) and a reset delay time of 40 µs (how long it takes to deassert $\overline{\text{RESET}}$). \boxtimes 9-3 and \boxtimes 9-4 are the results of the described application where the measured propagation delay and reset delay time are shown respectively.

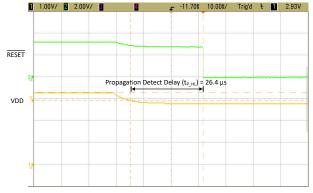
For the requirement of a maximum output current, an external pull-up resistor needs to be selected so that the current through the external pull-up resistor exceeds no more than 150 μ A. When the reset output is low, the voltage drop across the external pull-up resistor is equal to VDD. Ohm's law is used to calculate the minimum resistor value. The resistor needs to be greater than 22 k Ω in order to pull less than 150 μ A in the reset asserted low condition. A resistor value of 30.1 k Ω was selected to accomplish this.

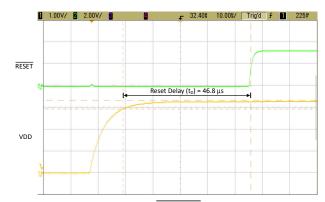
Note that this design does not account for tolerances.



9.2.3 Application Curves: TLV841EVM

These application curves are taken with the TLV841SADL01 part on the TLV841EVM. Please see the TLV841 User Guide for more information.





 \boxtimes 9-3. TLV841EVM Propagation Delay Time Delay (t_{D_HL})

図 9-4. TLV841EVM $\overline{\text{RESET}}$ Time Delay (t_D)

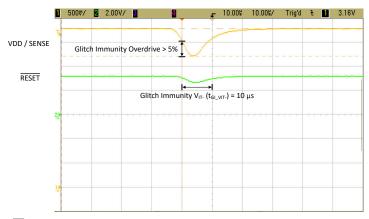


図 9-5. TLV841EVM SENSE Pin Glitch Immunity (t_{GI_VIT-})



10 Power Supply Recommendations

These devices are designed to operate from an input supply with a voltage range between 0.7 V and 5.5 V. TI recommends an input supply capacitor of 0.1 μ F between the VDD pin and GND pin. This device has a 6 V absolute maximum rating on the VDD pin. If the voltage supply providing power to VDD is susceptible to any large voltage transient that can exceed 6 V, additional precautions must be taken.

11 Layout

11.1 Layout Guidelines

Make sure that the connection to the VDD pin is low impedance. Good analog design practice recommends placing a minimum 0.1 μ F ceramic capacitor as near as possible to the VDD pin. If a capacitor is not connected to the CT pin (TLV841C), then minimize parasitic capacitance on this pin so the rest time delay is not adversely affected.

- Make sure that the connection to the VDD pin is low impedance. Good analog design practice is to place a greater than 0.1 μF ceramic capacitor as near as possible to the VDD pin.
- If a C_{CT_EXT} capacitor is used (TLV841C), place the capacitor as close as possible to the CT pin. If the CT pin is left unconnected, make sure to minimize the amount of parasitic capacitance on the pin to less than 5 pF.
- If a SENSE capacitor (C_{SENSE}) is used (TLV841S), place the capacitor as close as possible to the SENSE pin to further improve the noise immunity on the SENSE pin. Placing a 10 nF to 100 nF capacitor between the SENSE pin and GND can reduce the sensitivity to sensitivity to transient voltages on the monitored signal.
- Place the pull-up resistors on RESET pin as close to the pin as possible.

11.2 Layout Example

The layout example in 🗵 11-1 shows how the TLV841S is laid out on a printed circuit board (PCB) for every device variant.

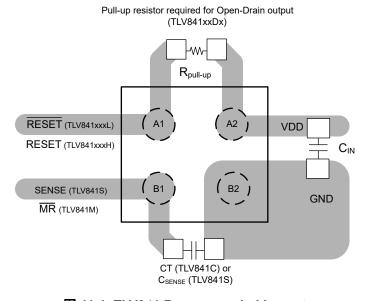


図 11-1. TLV841 Recommended Layout



12 Device and Documentation Support

12.1 Device Nomenclature

図 5-1 in セクション 5 and 表 12-1 shows how to decode the function of the device based on its part number.

表 12-1. Device Naming Convention

DESCRIPTION	NOMENCLATURE	VALUE				
Generic Part number	TLV841	TLV841				
Feature Option	S	SENSE pin option				
	С	CT pin for programmable delay using external capacitor				
	М	Manual Reset (MR) pin option				
Delay Option	A	40 μs (No internal reset time delay)				
	В	2 ms reset time delay				
	С	10 ms reset time delay				
	D	30 ms reset time delay				
	E	50 ms reset time delay				
	F	80 ms reset time delay				
	G	100 ms reset time delay				
	Н	150 ms reset time delay				
	I	200 ms reset time delay				
Variant code (Output Topology)	DL	Open-Drain, Active-Low				
	PL	Push-Pull, Active-Low				
	DH	Open-Drain, Active-High				
	PH	Push-Pull, Active-High				
Detect Voltage Option	## (two characters)	Example: 12 stands for 1.2 V threshold				
Package	YВН	DSBGA (4)				
Reel	R	Large Reel				

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12.2 Documentation Support

12.2.1 Related Documentation

The following related documents are available for download at www.ti.com:

- Optimizing Resistor Dividers at a Comparator Input, SLVA450
- Sensitivity Analysis for Power Supply Design, SLVA481
- Getting Started With TMS320C28x Digital Signal Controllers, SPRAAM0
- TLV841EVM-775 Evaluation Module User Guide, SBVU030
- C2000 Delfino Family of Microprocessors
- TMS320F2833x microcontroller, SPRS439

12.3 ドキュメントの更新通知を受け取る方法

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12.7 用語集

テキサス・インスツルメンツ用語集 この用語集には、用語や略語の一覧および定義が記載されています。

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TLV841SADL01YBHR	ACTIVE	DSBGA	YBH	4	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 125	9	Samples
TLV841SADL41YBHR	ACTIVE	DSBGA	YBH	4	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 125	Т	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV841SADL01YBHR	DSBGA	YBH	4	3000	180.0	8.4	0.84	0.84	0.48	4.0	8.0	Q1
TLV841SADL41YBHR	DSBGA	YBH	4	3000	180.0	8.4	0.84	0.84	0.48	4.0	8.0	Q1

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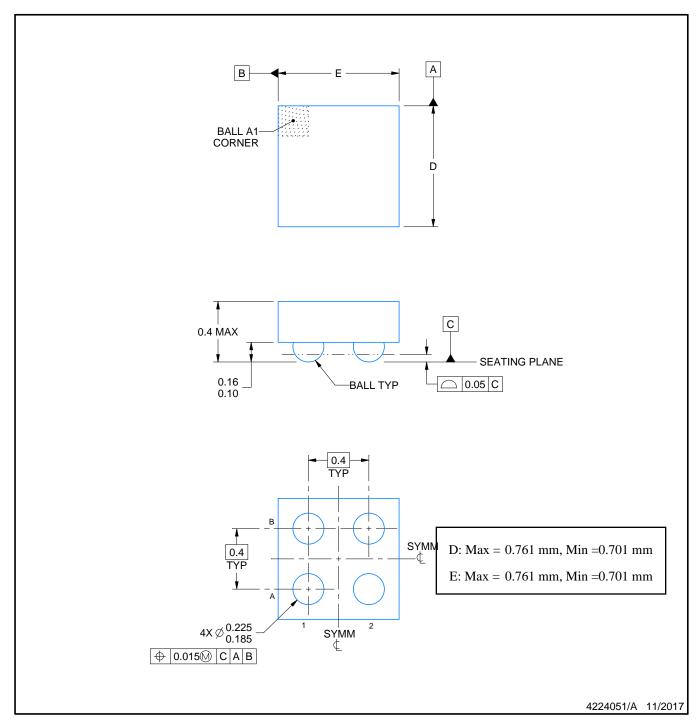


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV841SADL01YBHR	DSBGA	YBH	4	3000	182.0	182.0	20.0
TLV841SADL41YBHR	DSBGA	YBH	4	3000	182.0	182.0	20.0



DIE SIZE BALL GRID ARRAY



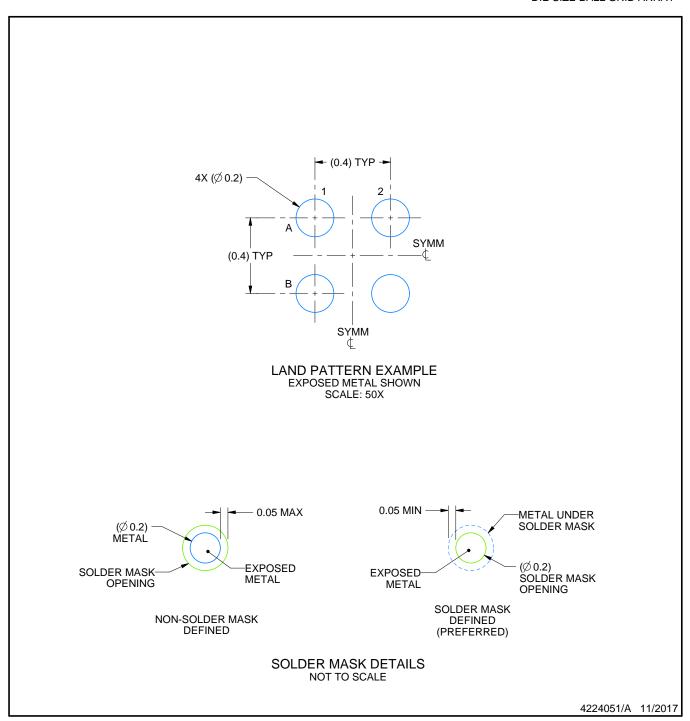
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY

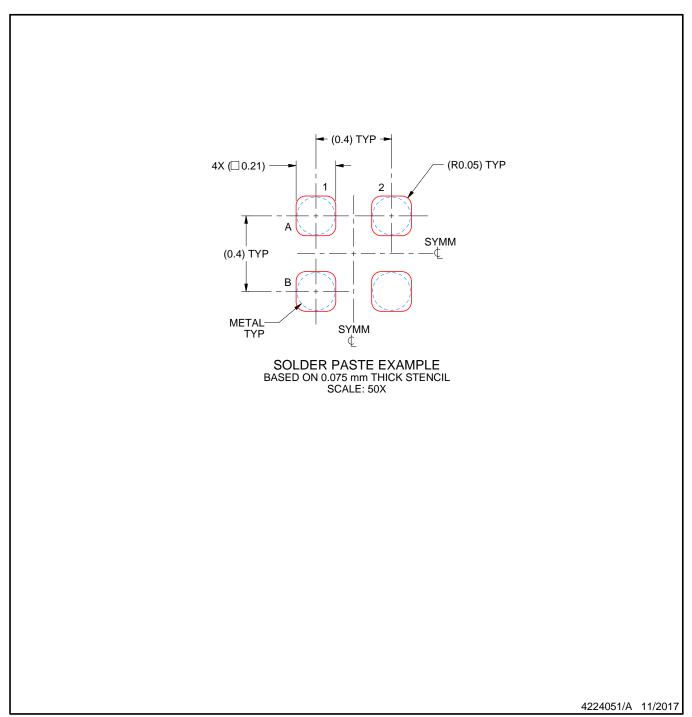


NOTES: (continued)

Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. See Texas Instruments Literature No. SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



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